

AMENDMENTS TO THE CLAIMS

1. - 2. (Canceled)

3. (Currently Amended) ~~The A~~ semiconductor device of ~~claim 2~~, comprising:
a p-type nitride semiconductor layer; and
a p-side electrode including a palladium oxide film connected to a surface of the p-
type nitride semiconductor layer, the palladium oxide film includes a platinum sulfide
structure type palladium oxide crystal;
wherein a percentage content of the platinum sulfide structure type palladium oxide
crystal included in the palladium oxide film is not less than about 50 %.

4. (Currently Amended) The semiconductor device of ~~claim 1~~ claim 3, wherein the p-
side electrode includes a palladium film on a surface of the palladium oxide film.

5. (Currently Amended) The semiconductor device of ~~claim 1~~ claim 3, wherein the p-
side electrode includes a platinum film on the palladium oxide film.

6. (Original) The semiconductor device of claim 4, wherein the p-side electrode
includes a first nickel containing film, made partly of a nickel oxide, on a surface of the
palladium film, and a gold film on a surface of the first nickel containing film.

7. (Original) The semiconductor device of claim 6, wherein the p-side electrode
includes a second nickel containing film, made partly of a nickel oxide, on the gold film.

8. (Original) The semiconductor device of claim 7, wherein mol fraction of oxygen contained in the first nickel containing film is less than the mol fraction in the second nickel containing film.

9. - 20. (Canceled)